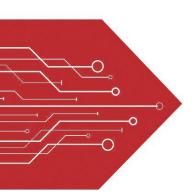
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

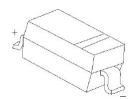
Broduct data speet





FEATURES

For use in low voltage, high frequency inverters Free wheeling, and polarity protection applications. **SOD-123**



MARKING: B5817W-MS: SJ

B5818W-MS:SK

B5819W-MS: SL

○**→**

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	B5817W-MS	B5818W-MS	B5819W-MS	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	30	40	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	20	30	40	V
RMS Reverse Voltage	V _{R(RMS)}	14	21	28	V
Average Rectified Output Current	Io	1		Α	
Peak Forward Surge Current @t=8.3ms	I _{FSM}	9		А	
Repetitive Peak Forward Current	I _{FRM}	1.5		Α	
Power Dissipation	Po	500		mW	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	200		°C/W	
Junction temperature	TJ	125		℃	
Storage Temperature	T _{STG}	-55~+150			$^{\circ}$

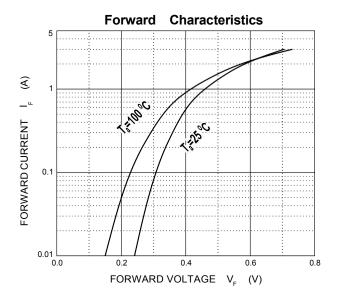
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

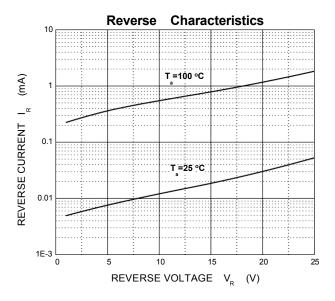
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 1mA B5817W-MS B5818W-MS B5819W-MS	20 30 40		V
Reverse voltage leakage current	I _R	V _R =20V B5817W-MS V _R =30V B5818W-MS V _R =40V B5819W-MS		1	mA
	V _F	B5817W-MS I _F =1A I _F =3A		0.45 0.75	V
Forward voltage		B5818W-MS I _F =1A I _F =3A		0.55 0.875	V
		B5819W-MS I _F =1A I _F =3A		0.6 0.9	V
Diode capacitance	C _D	V _R =4V, f=1MHz		120	pF

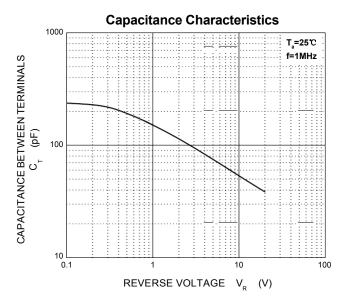


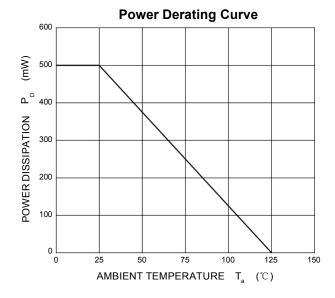
Semiconductor





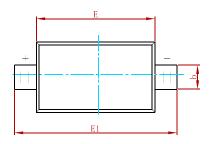


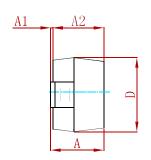


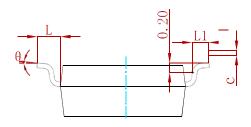




PACKAGE MECHANICAL DATA

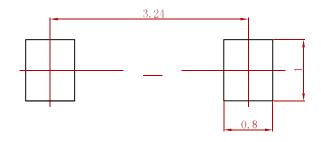






Cumbal	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.450	0.650	0.018	0.026	
С	0.080	0.150	0.003	0.006	
D	1.500	1.700	0.059	0.067	
E	2.600	2.800	0.102	0.110	
E1	3.550	3.850	0.140	0.152	
L	0.500 REF		0.020 REF		
L1	0.250	0.450	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
B5817W-MS	SOD-123	3000
B5818W-MS	SOD-123	3000
B5819W-MS	SOD-123	3000

Semiconductor



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